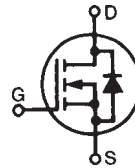


PolarHV™ HiPerFET Power MOSFET

IXFK 48N60P
IXFX 48N60P

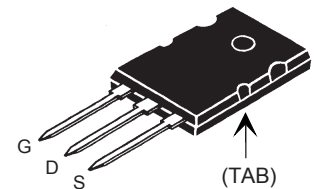
$V_{DSS} = 600 \text{ V}$
 $I_{D2} = 48 \text{ A}$
 $R_{DS(on)} \leq 135 \text{ m}\Omega$
 $t_{rr} \leq 200 \text{ ns}$

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode

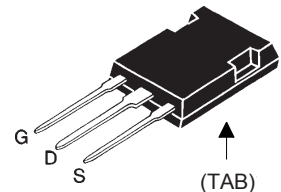


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	600	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$	600	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	48	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	110	A
I_{AR}	$T_C = 25^\circ\text{C}$	48	A
E_{AR}	$T_C = 25^\circ\text{C}$	70	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	2.0	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 4 \Omega$	20	V/ns
P_D	$T_C = 25^\circ\text{C}$	830	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque (TO-264)	1.13/10 Nm/lb.in.	
Weight	TO-264	10	g
	PLUS247	6	g
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
T_{SOLD}	Plastic body for 10 s	260	$^\circ\text{C}$

TO-264 (IXFK)



PLUS247 (IXFX)



G = Gate D = Drain
S = Source Tab = Drain

Features

- † International standard packages
- † Fast recovery diode
- † Unclamped Inductive Switching (UIS) rated
- † Low package inductance
- easy to drive and to protect

Advantages

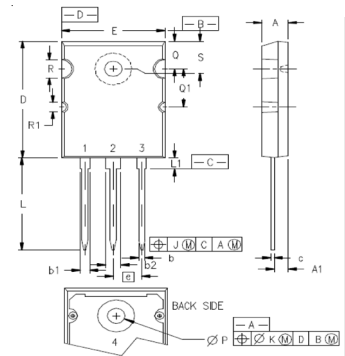
- † Easy to mount
- † Space savings
- † High power density

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	600		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 8 \text{ mA}$	3.0		5.0 V
I_{GSS}	$V_{GS} = \pm 30 \text{ V}_{DC}$, $V_{DS} = 0$			$\pm 200 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$ $T_J = 125^\circ\text{C}$			25 μA
				1000 μA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$			135 $\text{m}\Omega$

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 20\text{ V}; I_D = 0.5 I_{D25}$, pulse test	35	53	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		8860	pF
C_{oss}			850	pF
C_{rss}			60	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 I_{D25}$ $R_G = 2\ \Omega$ (External)		30	ns
t_r			25	ns
$t_{d(off)}$			85	ns
t_f			22	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$		150	nC
Q_{gs}			50	nC
Q_{gd}			50	nC
R_{thJC}	TO-264 and PLUS247			0.15 °C/W
R_{thCs}			0.15	°C/W

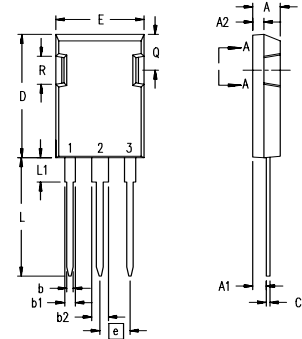
Source-Drain Diode

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{ V}$			48 A
I_{SM}	Repetitive			110 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5 V
t_{rr}	$I_F = 25\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 100\text{ V}$			200 ns
Q_{RM}			0.8	μC
I_{RM}			6.0	A

TO-264 (IXFK) Outline


- 1 - GATE
2, 4 - DRAIN (COLLECTOR)
3 - SOURCE (EMITTER)

SYM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215 BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
ØP	.122	.138	3.10	3.51
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

PLUS 247™ (IXFX) Outline


- Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)
4 - Drain (Collector)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405B2	6,759,692
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2

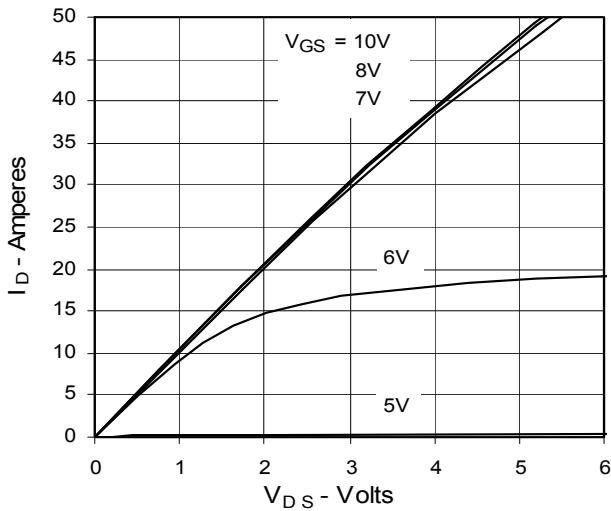
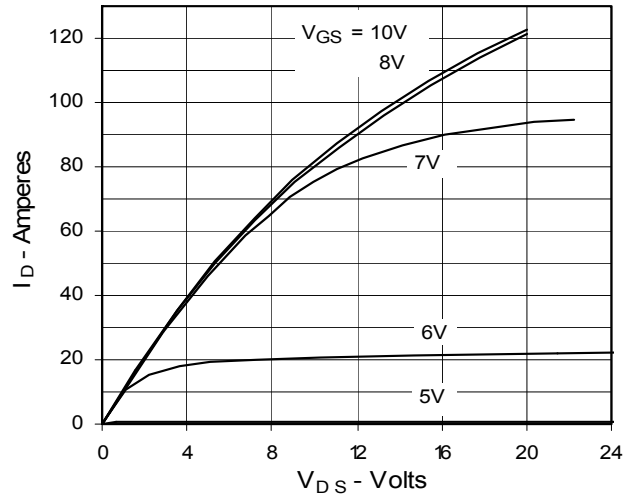
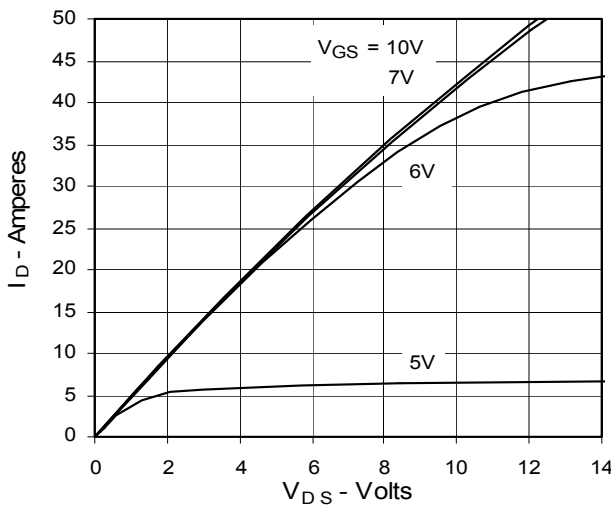
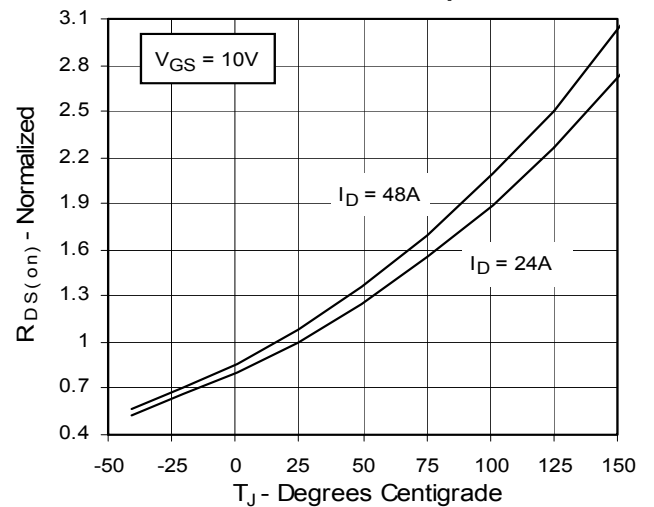
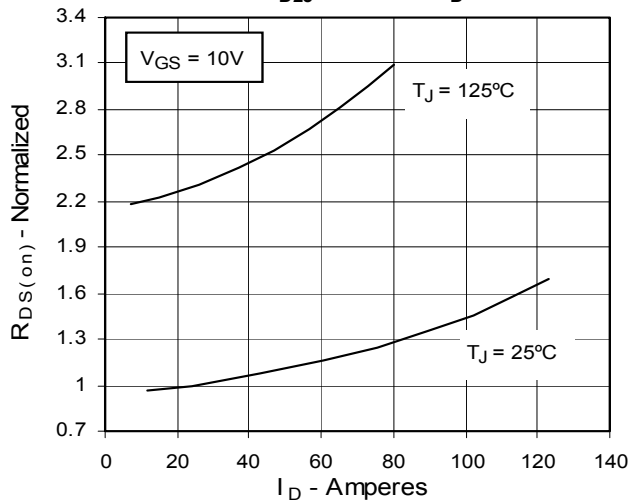
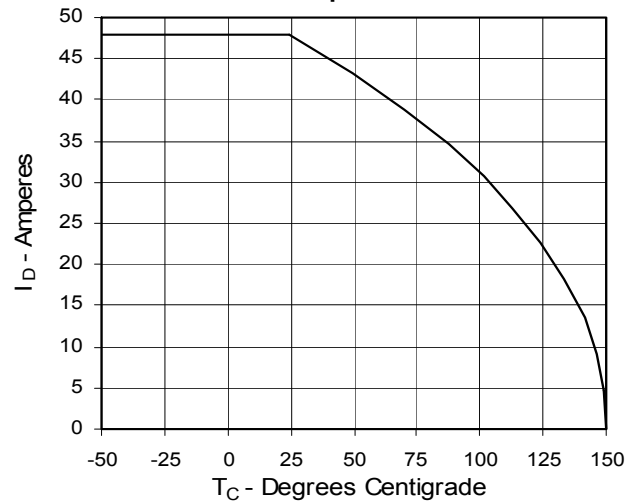
**Fig. 1. Output Characteristics
@ 25°C**

**Fig. 2. Extended Output Characteristics
@ 25°C**

**Fig. 3. Output Characteristics
@ 125°C**

**Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25}
Value vs. Junction Temperature**

**Fig. 5. $R_{DS(on)}$ Normalized to
0.5 I_{D25} Value vs. I_D**

**Fig. 6. Drain Current vs. Case
Temperature**


Fig. 7. Input Admittance

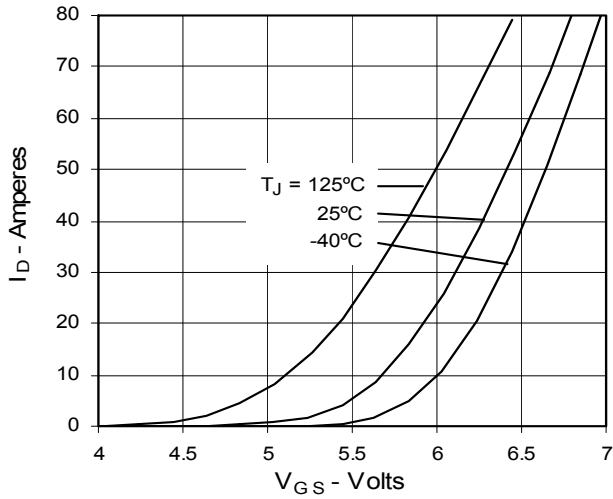


Fig. 8. Transconductance

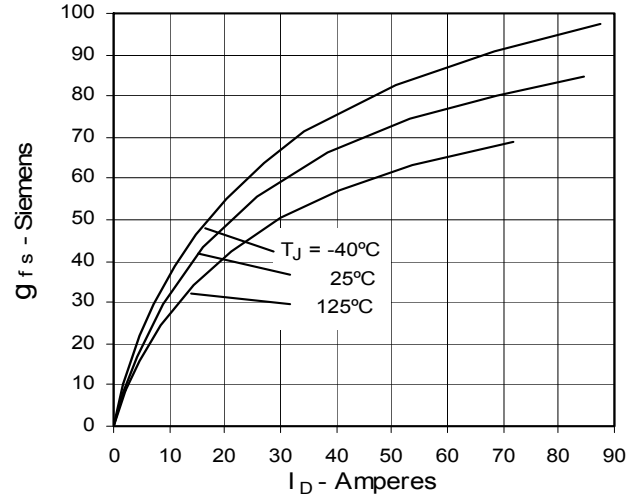


Fig. 9. Source Current vs. Source-To-Drain Voltage

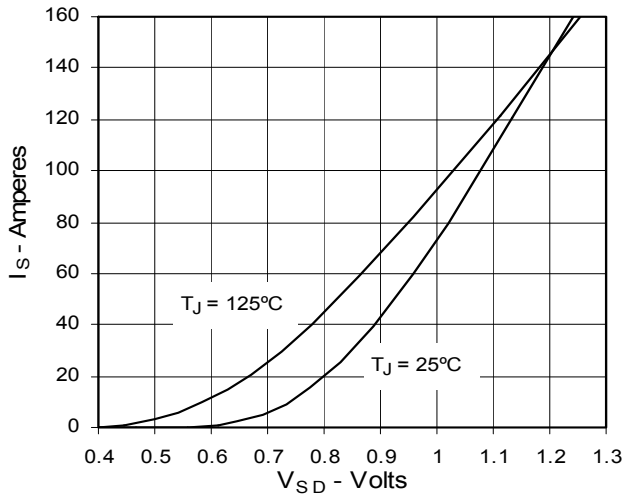


Fig. 10. Gate Charge

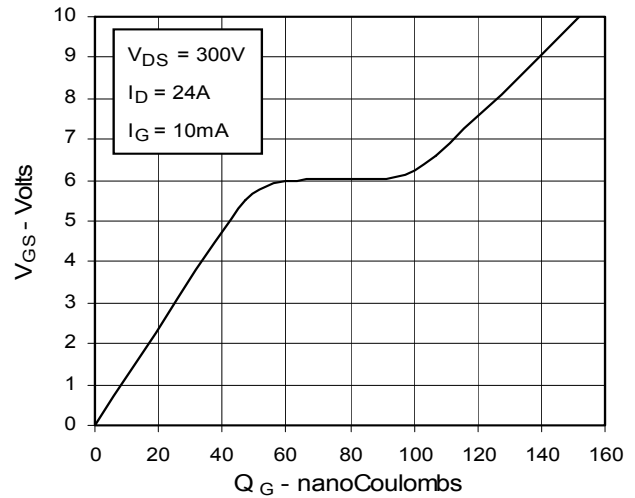


Fig. 11. Capacitance

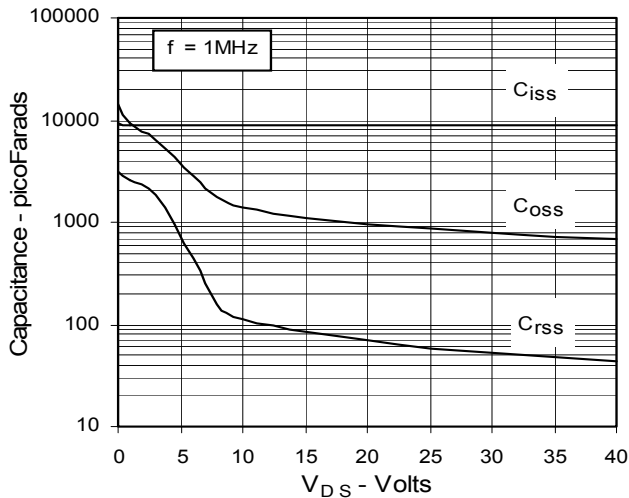


Fig. 13. Maximum Transient Thermal Resistance

